

Abstract of the Disclosure

For patterning an IC (integrated circuit) material, a rigid organic under-layer is formed over the IC material, and the rigid organic under-layer is patterned to form a rigid organic mask structure. In addition, the rigid organic mask structure is trimmed to lower
5 a critical dimension of the rigid organic mask structure beyond the limitations of traditional BARC mask structures. Any portion of the IC material not under the rigid organic mask structure is etched away to form an IC structure.